• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

■AEC-Q101 Qualified

■Low $R_{DS(ON)}$ to minimize conductive loss

■Low Gate Charge for fast switching

■Low Thermal resistance

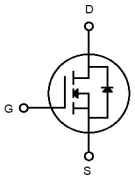
•Application

■BLDC Motor driver

■DC-DC

■Load Switch

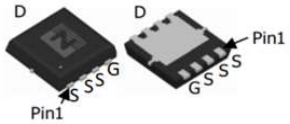
• Product Summary



V_{DS}= 80V

$R_{DS(ON)}$ = 6.3mΩ

I_D= 78A



DFN3*3

RoHS

REACH COMPLIANT

HF

•Ordering Information:

Part NO.	ZMSA080N08HM
Marking	080N08H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	5000

•Absolute Maximum Ratings (T_A=25°C,unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Max.	Unit
Drain-Source Voltage	V_{DS}		-	80	V
Gate-Source Voltage①	V_{GS}		-20	20	V
Continuous Drain Current	I_D	V_{GS}=10V,T_C=25℃	-	78	A
	I_D	V_{GS}=10V,T_C=75°C	-	64	A
	I_D	V_{GS}=10V,T_C=100°C	-	55	A
Pulsed Drain Current ①	I_{DM}	Pulsed; t_p ≤ 10 μs; T_C = 25 °C;	-	312	A
Total Power Dissipation	P_D	T_C=25℃	-	79	W
Total Power Dissipation	P_D	T_A=25℃	-	2.5	W
Operating Junction Temperature	T_J		-55	175	℃
Storage Temperature	T_{STG}		-55	175	℃
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, V_{GS}=10V, Rg=25Ω,	-	72	mJ
		L=0.3mH, V_{GS}=10V, Rg=25Ω,	-	116	mJ
ESD Level (HBM)	CLASS 2				

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.9	°C/W
Thermal resistance, junction-ambient	R_{thJA} ②	-	-	60	°C/W
Soldering temperature	Tsold	-	-	260	°C

•Electronic Characteristics (Tj=25°C,unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =250uA	80	-	-	V
Gate Threshold Voltage	$VGS_{(TH)}$	V_{GS}=V_{DS}, I_D=250uA	2	2.7	4	V
Drain-Source Leakage Current	I_{DSS}	V_{GS}=0V, V_{DS}=80V	-	-	1	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS} =0V	-	-	±100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=10A, Tj=25°C	-	6.3	7.6	mΩ
		V_{GS}=10V, I_D=10A, Tj=175°C	-	10.6	-	mΩ
Forward Transconductance	g_{FS}	V_{DS} =5V, I_{SD} =5A	-	10	-	S
Diode Forward Voltage	V_{FSD}	V_{GS} =0V,I_{SD} =10A	-	-	1.3	V

•Dynamic characteristics (Tj=25°C,unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	Ciss	f = 1MHz, V_{DS}=40V, V_{GS}=0V	-	1711	-	pF
Output capacitance	Coss		-	317	-	
Reverse transfer capacitance	Crss		-	14	-	
Gate Risistance	Rg	f = 1MHz	-	1.9	-	Ω
Total gate charge	Qg	V_{DD} = 40V,I_D = 10A, V_{GS} = 10V	-	35.7	-	nC
Gate - Source charge	Qgs		-	6.4	-	
Gate - Drain charge	Qgd		-	12.3	-	
Turn-ON Delay time	$t_{D(on)}$	V_{GS}=10V,V_{DS}=40V,R_G =3.3 Ω, I_D =10A	-	11	-	ns
Turn-ON Rise time	t_r		-	31	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	28	-	ns
Turn-Off Fall time	t_f		-	31	-	ns
Reverse Recovery Time	t_{rr}	V_{DD}=40V, dI_S/dt = 100A/us, I_S=10A	-	36	-	ns
Reverse Recovery Charge	Q_{rr}		-	43	-	nC

Fig.1 Gate-source voltage as a function of gate charge;Typical values;Tj=25°C

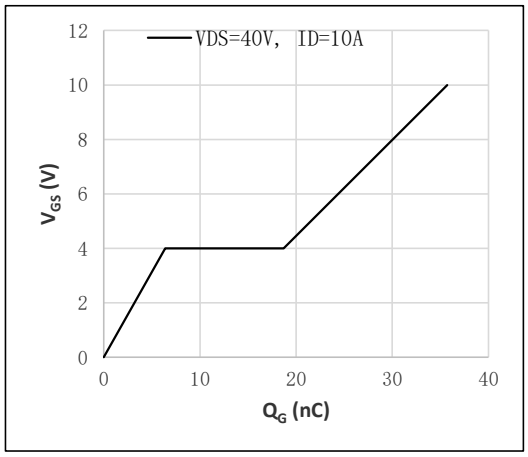


Fig.2 Input, output and reverse transfer capacitances as a function of drain-source voltage;Typical values;Tj=25°C

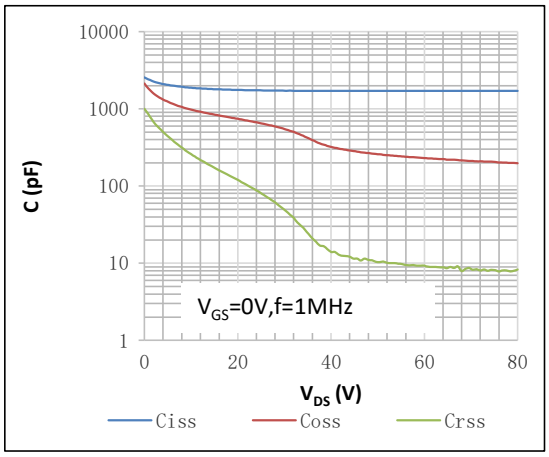


Fig.3 Output characteristics: drain current as a function of drain-source voltage;Typical values; Tj=25°C

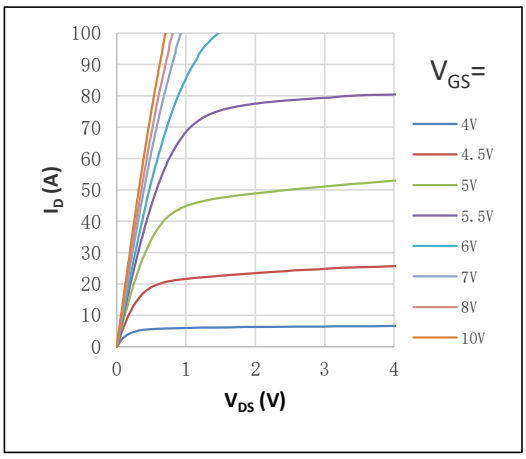


Fig.4 Output characteristics: drain current as a function of drain-source voltage;Typical values:Expanded curve;Tj=25°C

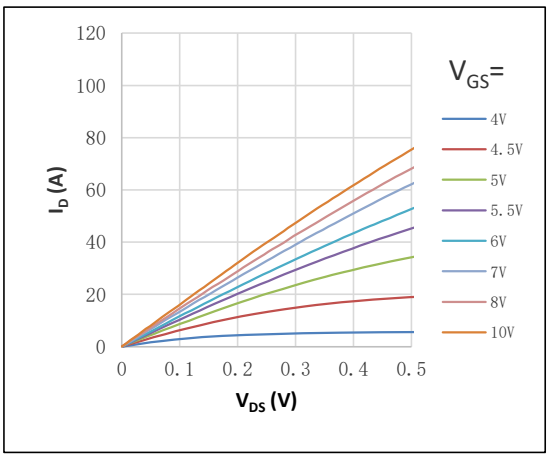


Fig.5 Gate-source threshold voltage as a function of junction temperature;Typical values

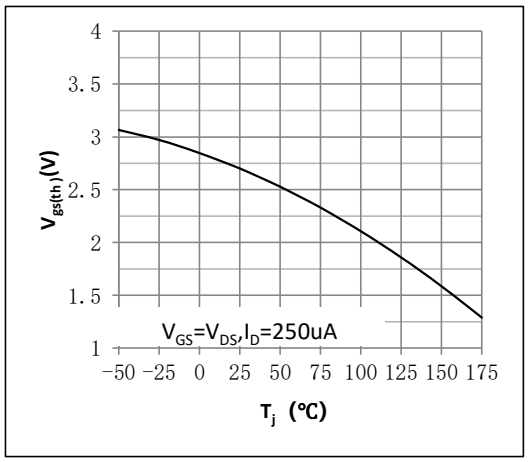


Fig.6 Drain-source on-state resistance as a function of drain current;Typical values;Tj=25°C

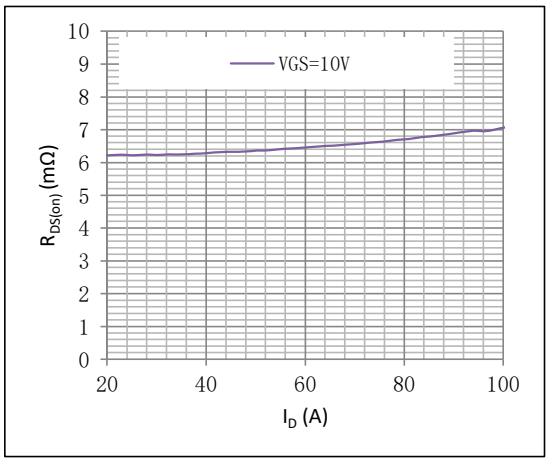


Fig.7 Drain-source on-state resistance as a function of gate-source voltage;Typical values

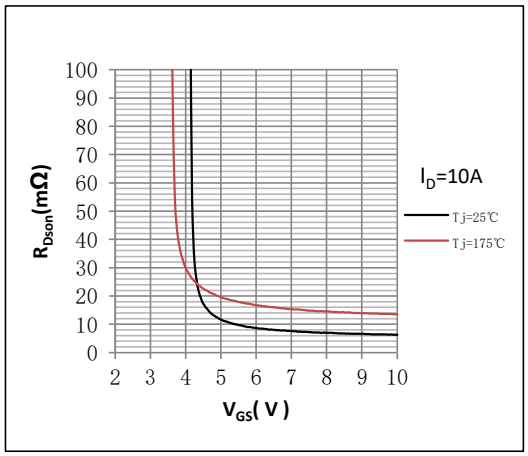


Figure 9. Source (diode forward) current as a function of source-drain (diode forward) voltage ;Typical values

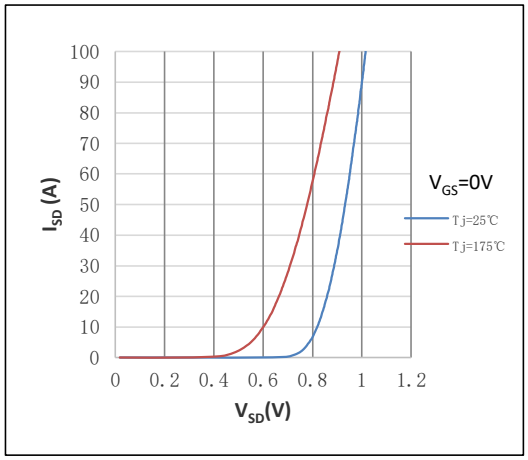


Fig.11 Safe operating area: continuous and peak drain currents as a function of drain-source voltage;Calculative values

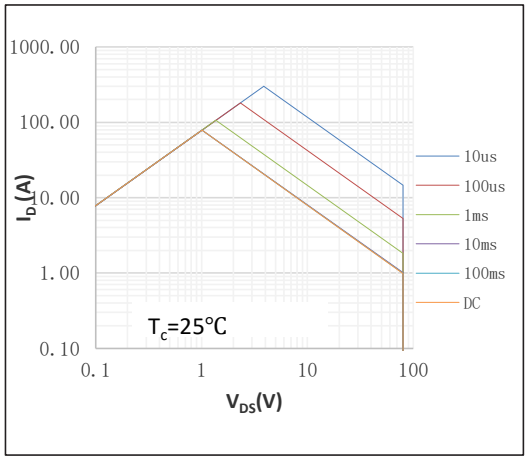


Fig.8 Normalized drain-source on-state resistance factor as a function of junction temperature;Typical values
Normalized On-Resistance=RDSon/RDSon(25 ℃)

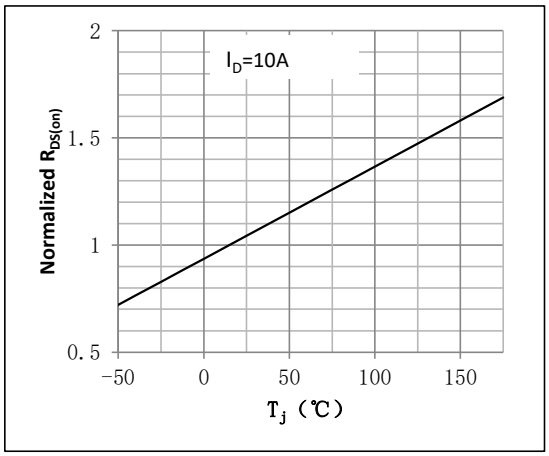


Figure 10. Transfer characteristics: drain current as a function of gate-source voltage;Typical values

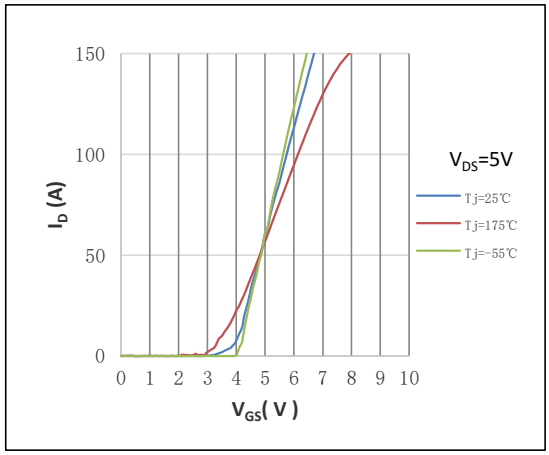


Fig.12 Continuous drain current as a function of case temperaturease③;Calculative values

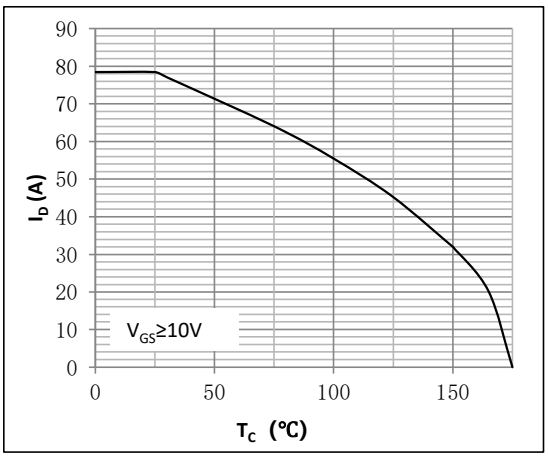


Fig.13 Drain-source breakdown voltage as a function of junction temperature;Typical values
Normalized BVDSS=BVDSS/BVDSS(25°C)

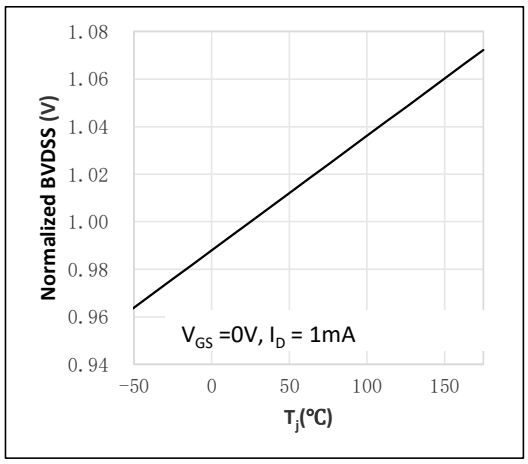


Fig.14 Normalized total power dissipation as a function of case temperature;Calculative values
Normalized Power Dissipation=Pd/Pd(25°C)

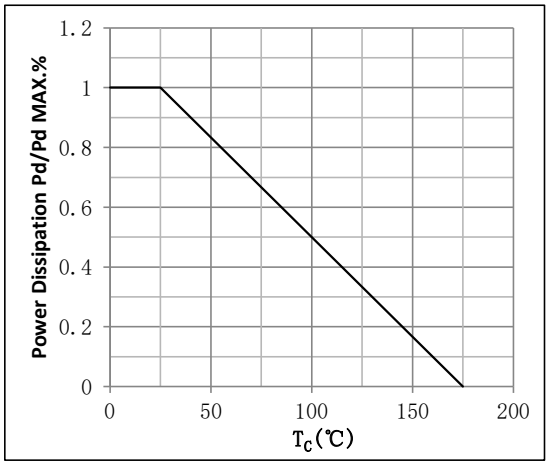
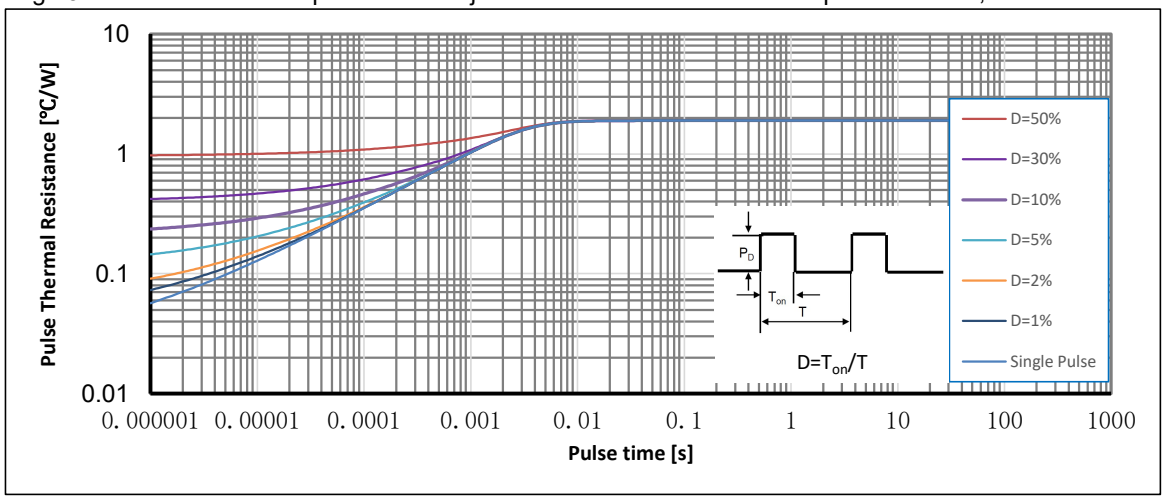
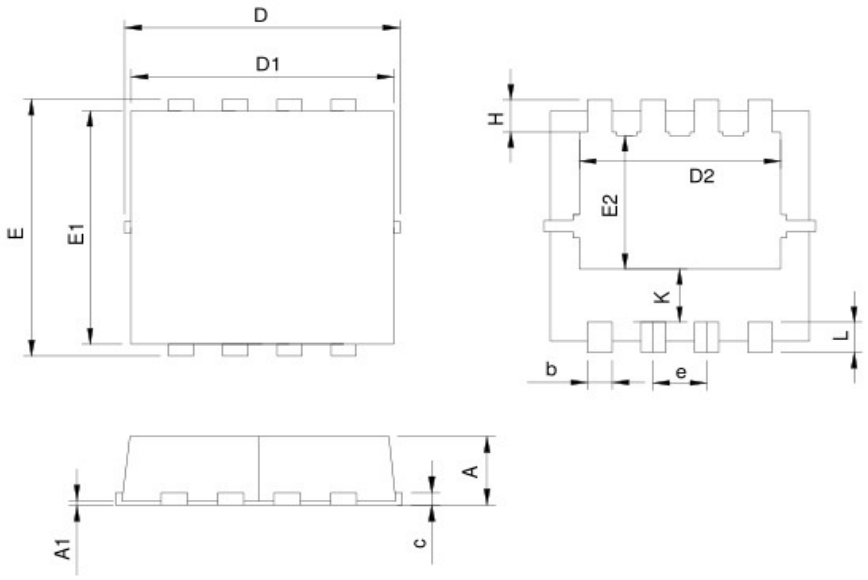


Fig.15 Transient thermal impedance from junction to case as a function of pulse duration; max values

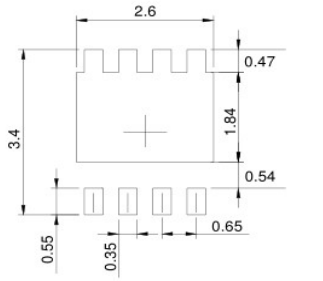


●DFN3*3 Package Outline



SYMBOL	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm

Note:

① Pulse : VGS=+20V/-20V, Duty cycle=50%,Tj=175℃, t=1000 hours; For DC， the following test conditions can be passed: VGS=+20V/-10V, Tj=175℃, t=1000 hours；

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate；

③Practically the current will be limited by PCB, thermal design and operating temperature. VGS=10V.

Disclaimer

Version	Date	Change
A	2025/2/21	New